

Features

- Transient protection for gigabit ethernet lines-to-lines
- Provide transient protection for the protected differential line pair to
 IEC 61000-4-2 (ESD) ±30kV (air/contact)
 IEC 61000-4-4 (EFT) 80A (5/50ns)
 IEC 61000-4-5 (Lightning) 45A (8/20µs)
- DFN3020P10E package
- Specific pin out for easy board layout
- Fast turn-on and low clamping voltage
- Low capacitance for high speed interfaces
- For low operating voltage applications: 2.5V
- Low leakage current
- Solid-state silicon-avalanche and active circuit triggering technology
- Green part

Applications

- WAN/LAN device
- 10/100/1000 ethernet
- Switching systems
- Computers
- Instruments

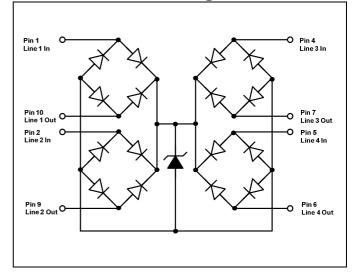
Description

AZ3225-08F is a design which includes surge rated diode arrays to protect high speed data interfaces in an electronic system. The AZ3225-08F has been specifically designed to protect sensitive components which are connected to data and transmission lines from over-voltage damage caused by Electrostatic Discharging (ESD), Electrical Fast Transients (EFT), and Lightning.

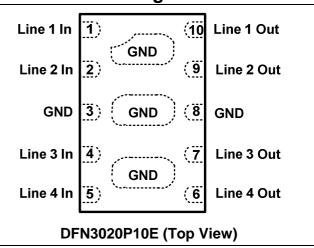
AZ3225-08F is a unique design which includes surge rated, low capacitance steering diodes and a unique design of clamping cell which is an equivalent TVS diode in a single package. During transient conditions, the proprietary clamping cells prevent over-voltage on the signal lines, protecting any downstream components.

AZ3225-08F may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (\pm 15kV air, \pm 8kV contact discharge).

Circuit Diagram



Pin Configuration



1



Specifications

Absolute Maximum Ratings (T_A = 25°C, unless otherwise specified)				
Parameter	Symbol	Rating	Unit	
Peak Pulse Current ($t_p = 8/20\mu s$) (Note 1)	I _{PP}	45	А	
ESD per IEC 61000-4-2 (Air)	V _{ESD-1}	±30	kV	
ESD per IEC 61000-4-2 (Contact)	V _{ESD-2}	±30	ĸv	
Lead Soldering Temperature	T _{SOL}	260 (10 sec.)	°C	
Operating Temperature	T _{OP}	-55 to +125	°C	
Storage Temperature	T _{STO}	-55 to +150	°C	

Electrical Characteristics						
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Reverse Stand-Off Voltage	V_{RWM}	Between I/O pins, T=25 °C.			2.5	V
Channel Leakage Current	I _{Leak}	V_{RWM} = 2.5V, T=25 °C, between I/O pins.			0.5	μA
Reverse Breakdown Voltage	V_{BV}	I _{BV} = 1mA, T=25 °C, between I/O pins.	3		7	V
Surge Clamping Voltage V _{CL-surge}		I _{PP} =5A, t _p =8/20μs, T=25 °C, between I/O pins.			7	V
	$V_{CL-surge}$	I _{PP} =25A, t _p =8/20μs, T=25 °C, between I/O pins.			11.5	V
		I_{PP} =45A, t_p =8/20µs, T=25 °C, line-to-line, two I/O pins connected together on each line (Note 1).			11.5	V
ESD Clamping Voltage (Note 2)	V _{CL-ESD}	IEC 61000-4-2 +8kV (I_{TLP} = 16A), T=25 °C, contact mode, between I/O pins.		8		V
ESD Dynamic Turn-on Resistance	$R_{dynamic}$	IEC 61000-4-2 0~+8kV, T=25 °C, contact mode, between I/O pins.		0.18		Ω
Channel Input Capacitance	C _{IN}	$V_{IN} = 0V$, f = 1MHz, T=25 °C, between I/O pins.		1.2	1.5	pF

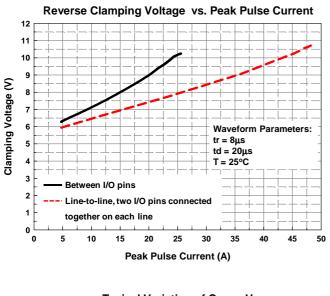
Note 1: Ratings with two pins connected together per the recommended configuration (i.e. pin-1 connected to pin-10, pin-2 connected to pin-9, pin-4 connected to pin-7, and pin-5 connected to pin-6).

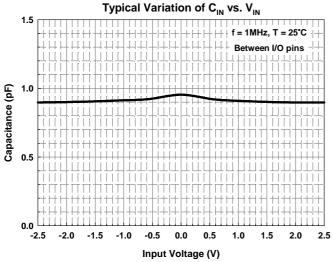
Note 2: ESD Clamping Voltage was measured by Transmission Line Pulsing (TLP) System.

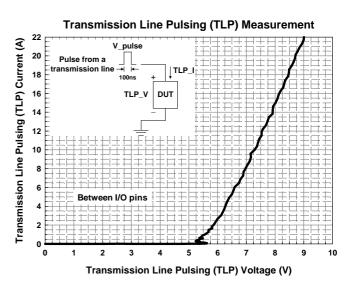
TLP conditions: Z_0 = 50 Ω , t_p = 100ns, t_r = 1ns.



Typical Characteristics









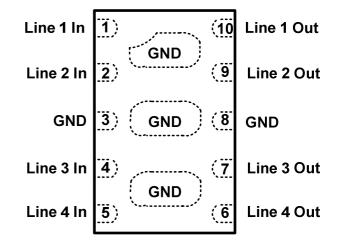
Applications Information

The AZ3225-08F is designed to protect four high speed data lines operating at 2.5 volts to against system ESD/EFT/Lightning pulses by clamping them to an acceptable reference.

The AZ3225-08F designed with a flow through pin configuration is shown in Fig. 1. Fig. 2 shows a typical PCB layout example with AZ3225-08F for ESD/EFT/Lightning protection. In the Gigabit Ethernet application, pin-1, -2, -4, and pin-5 should be connected to pin-10, -9, -7, and pin-6 respectively. The traces should be unbroken and run under the device as shown. To get minimum parasitic inductance, the path length should keep as short as possible. Pin-3, -8 and the three center tabs are electrically connected, which should be left floating (i.e. not connected to ground) in the Ethernet application. Fig. 3 shows a typical Gigabit Ethernet protection circuit with AZ3225-08F.

In order to obtain enough suppression of ESD induced transient, a good circuit board is critical. Thus, the following guidelines are recommended:

- Minimize the path length between the protected lines and the AZ3225-08F.
- Place the AZ3225-08F near the input terminals or connectors to restrict transient coupling.
- The ESD current return path should be kept as short as possible.
- NEVER route critical signals near board edges and near the lines which the ESD transience easily injects to.





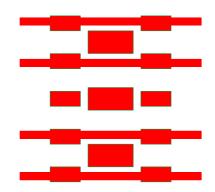


Fig. 2 Layout example of AZ3225-08F.



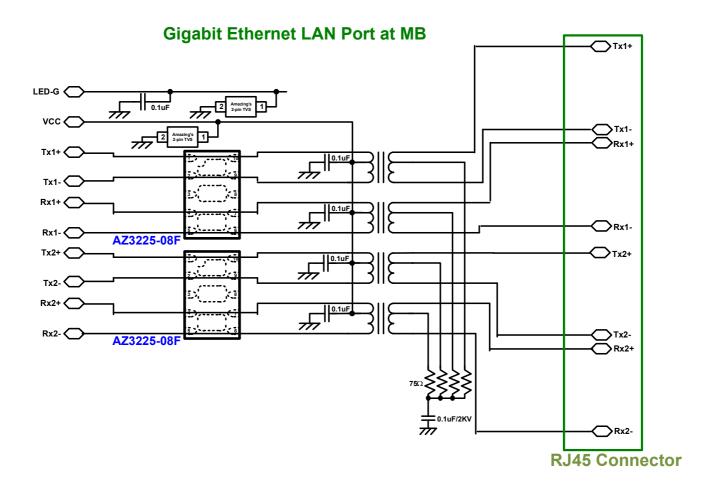
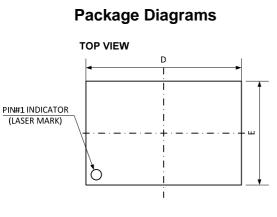


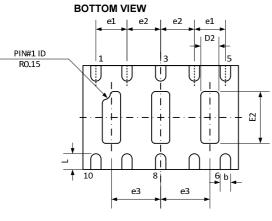
Fig. 3 Gigabit Ethernet surge protection circuit with AZ3225-08F.



Mechanical Details



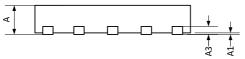
DFN3020P10E



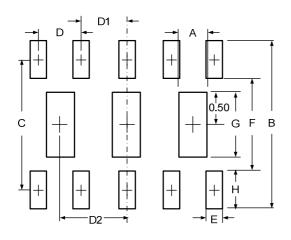
Symbol	Millimeters				
Symbol	Min.	Nom.	Max.		
Α	0.510	0.600			
A1	0.000 0.020 0.0		0.050		
A3	0.153 REF				
b	0.150 0.200 0.2		0.250		
D	2.900	3.000	3.100		
E	1.900	2.000	2.100		
e1	0.600 BSC				
e2	0.650 BSC				
e3	0.950 BSC				
D2	0.250	0.350	0.450		
E2	0.950	1.000	1.050		
L	0.250	0.300	0.350		

Package Dimensions

SIDE VIEW



Land Layout



Dimensions			
Index	Millimeters		
A	0.40		
В	2.56		
С	1.98		
D	0.60		
D1	0.65		
D2	0.95		
E	0.25		
F	1.40		
G	1.00		
Н	0.58		



Marking Code



322F = Device Code W = Date Code XX = Control Code

Part Number	Marking Code
AZ3225-08F.R7G	322F
(Green Part)	WXXG

Note : Green means Pb-free, RoHS, and Halogen free compliant.

Ordering Information

PN#	Material	Туре	Reel size	MOQ	MOQ/internal box	MOQ/carton
AZ3225-08F.R7G	Green	T/R	7 inch	3,000/reel	4 reels=12,000/box	6 boxes=72,000/carton

Revision History

Revision	Modification Description
Revision 2019/11/28	Formal Release